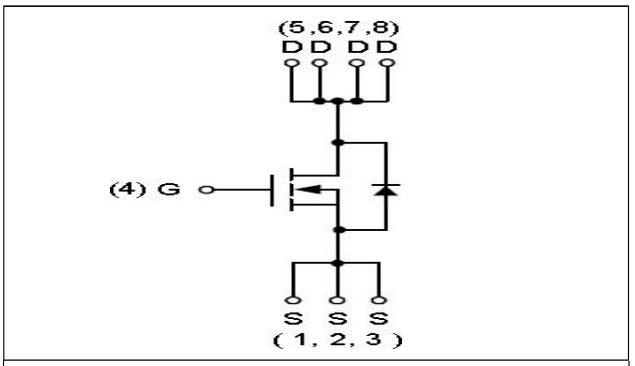
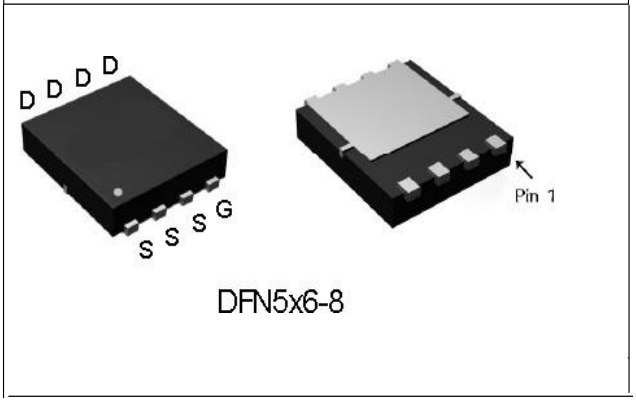
深圳市诚芯微科技股份有限公司
SHENZHEN CHENGXINWEI TECHNOLOGY CO., LTD.

N-channel Enhancement Mode Mosfet CX010N10

DESCRIPTION

The CX010N10 is the high celldensity trenched N-CH MOSFETs,which provide excellent RDSON and GATE charge for mosr of the synchronous Rectification





GENERAL FEATURES

- VDS= 100V
  RDS(ON) =15m Ω @ VGS= 10V
  RDS(ON) =17m Ω @ VGS=4.5V
- Low RDS(on) & FOM
- Extremely low switching loss
- Excellent reliability and uniformity
- Fast switching and soft recovery

Application

- PD charger
- Switching voltage regulator
- DC-DC convertor
- Switched mode power supply

■ Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	100	V
Gate-source Voltage		V_{GS}	±20	V
Drain Current	T_C=25℃	I_D	50	A
	T_C=100℃		32	
Pulsed Drain Current [A]		I_{DM}	200	A
Total Power Dissipation	T_C=25℃	P_D	78	W
Single Pulse Avalanche Energy [B]		E_{AS}	80	mJ
Thermal Resistance Junction-to-Case [C]		RθJC	1.6	℃/ W
Thermal resistance, junction-ambient4)		RθJA	30	℃/ W
Junction and Storage Temperature Range		T_J ,TST G	-55～+150	℃